

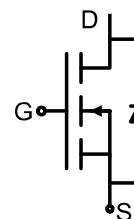
AP3100A

N-Channel Enhancement Mosfet



Feature

- 30V,8A
 $R_{DS(ON)} < 12m\Omega @ V_{GS}=10V$ TYP:9.8m Ω
 $R_{DS(ON)} < 16m\Omega @ V_{GS}=4.5V$ TYP:13.5 m Ω
- Advanced Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram

Application

- PWM applications
- Load Switch
- Power management



SOT-23-3 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
3100A	AP3100A	SOT23-3	7 inch	-	3000

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a=25^{\circ}C$)	I_D	8	A
Continuous Drain Current ($T_a=100^{\circ}C$)	I_D	6.2	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	40	A
Power Dissipation	P_D	1.6	W
Thermal Resistance from Junction to Ambient ⁽³⁾	$R_{\theta JA}$	78	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

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MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	30	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =30V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V,V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽²⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2.5	V
Drain-source on-resistance ⁽²⁾	R _{DS(on)}	V _{GS} =10V, I _D =8A	-	9.8	12	mΩ
		V _{GS} =4.5V, I _D =4A	-	13.5	16	
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f =1MHz	-	1140	-	pF
Output Capacitance	C _{oss}		-	175	-	
Reverse Transfer Capacitance	C _{rss}		-	151	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =15V, I _D =4A, V _{GS} =10V, R _G =3Ω	-	15	-	ns
Turn-on rise time	t _r		-	19	-	
Turn-off delay time	t _{d(off)}		-	35	-	
Turn-off fall time	t _f		-	21	-	
Total Gate Charge	Q _g	V _{DS} =15V, I _D =4A, V _{GS} =10V	-	13.3	-	nC
Gate-Source Charge	Q _{gs}		-	3.1	-	
Gate-Drain Charge	Q _{gd}		-	5	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽²⁾	V _{DS}	V _{GS} =0V, I _S =8A	-	-	1.2	V
Diode Forward current ⁽³⁾	I _S		-	-	8	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. Pulse Test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. Surface Mounted on FR4 Board, $t \leq 10$ sec

Test Circuit

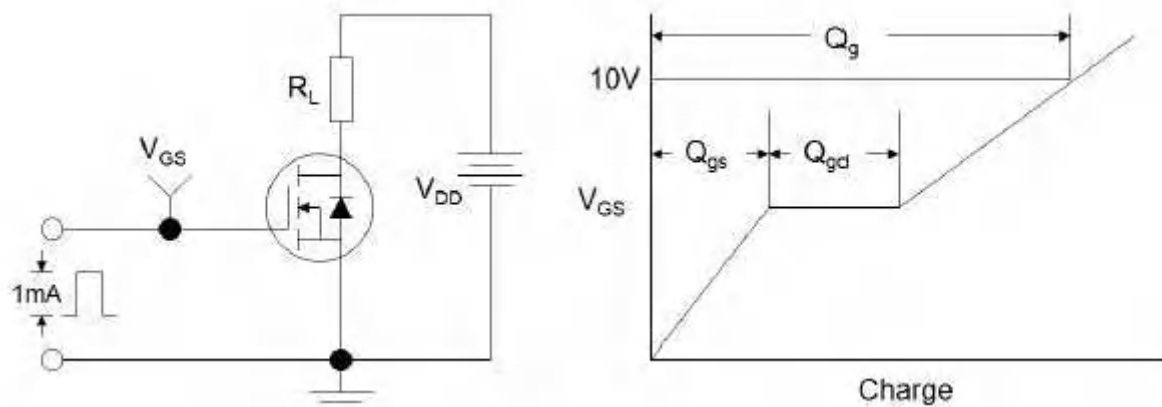


Figure1:Gate Charge Test Circuit & Waveform

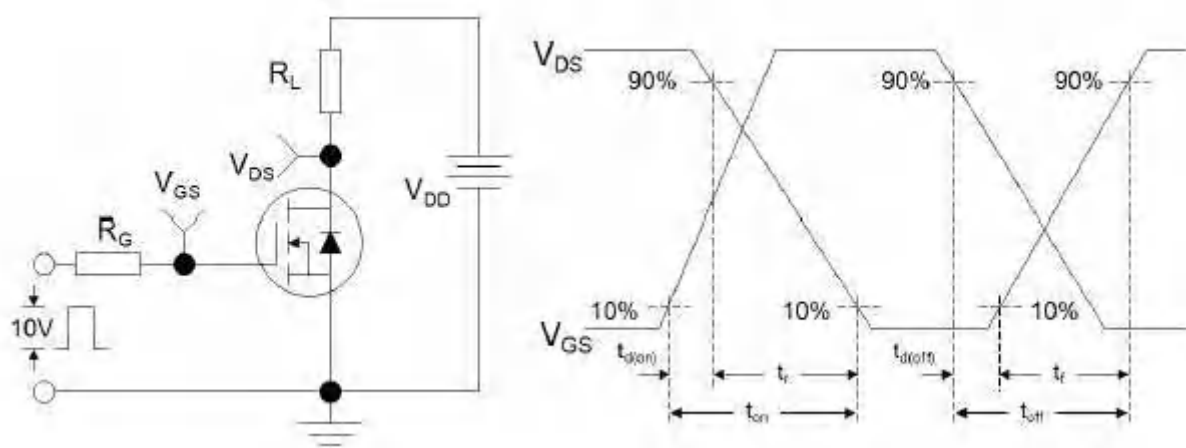


Figure 2: Resistive Switching Test Circuit & Waveforms

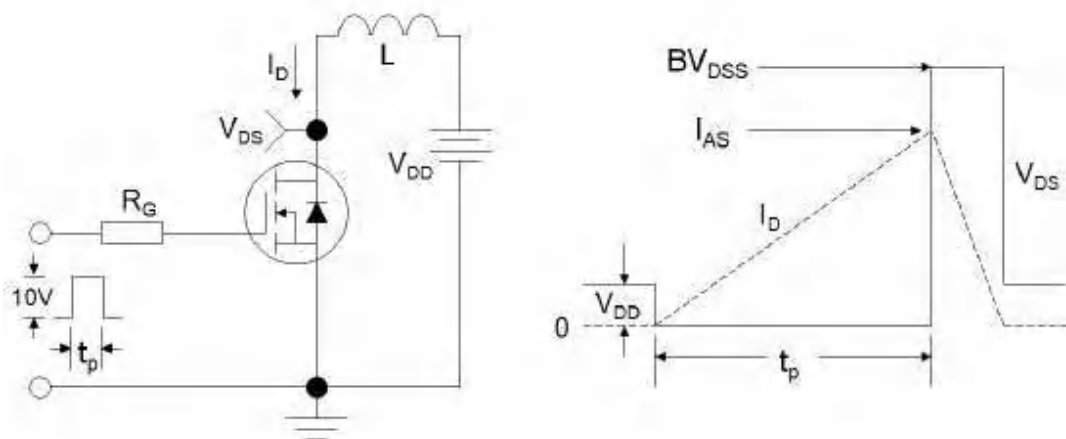


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Typical Performance Characteristics

Figure1: Output Characteristics

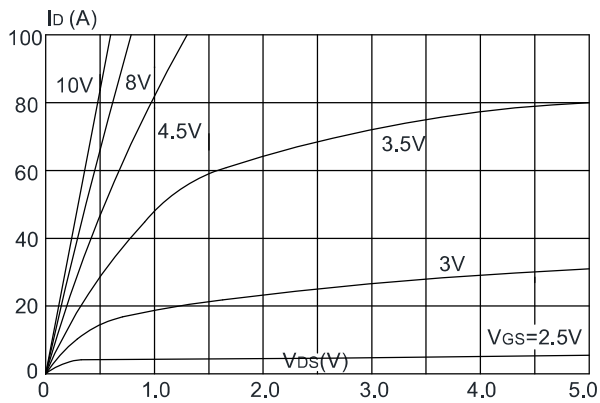


Figure 2: Typical Transfer Characteristics

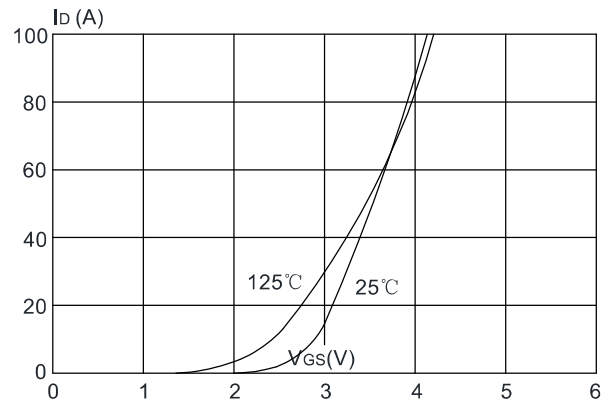


Figure 3: On-resistance vs. Drain Current

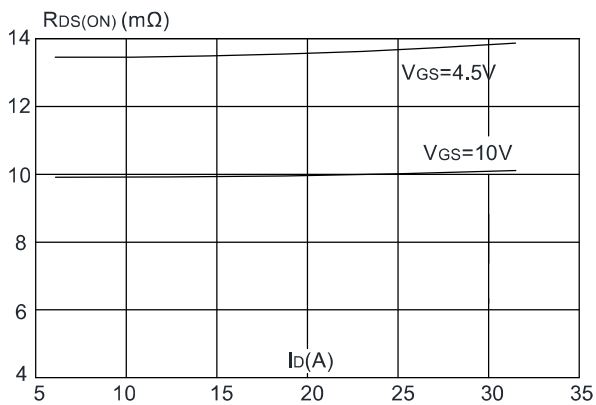


Figure 4: Body Diode Characteristics

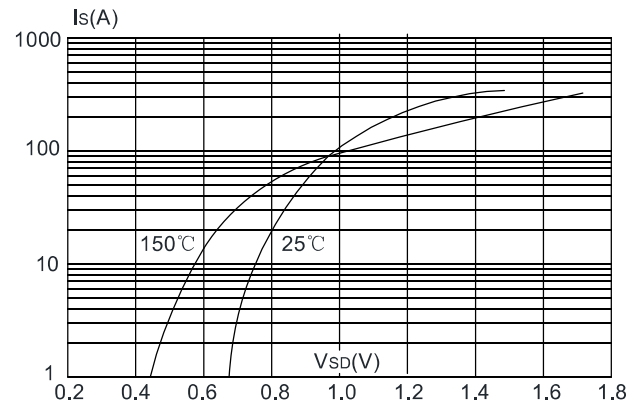


Figure 5: Gate Charge Characteristics

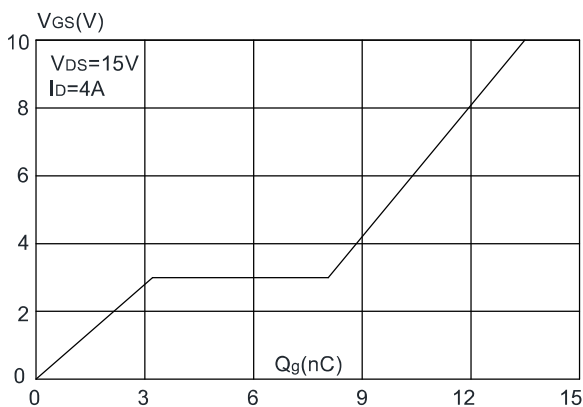


Figure 6: Capacitance Characteristics

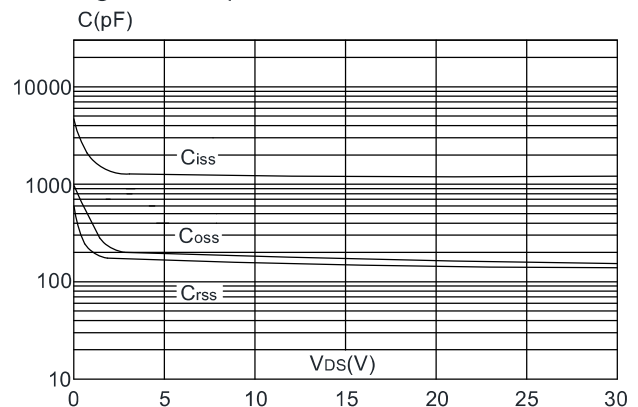


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

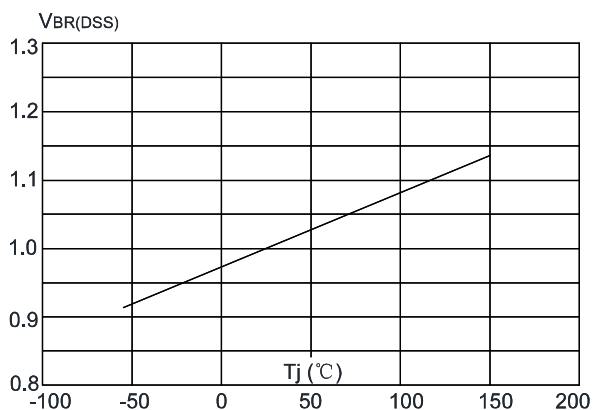


Figure 8: Normalized on Resistance vs. Junction Temperature

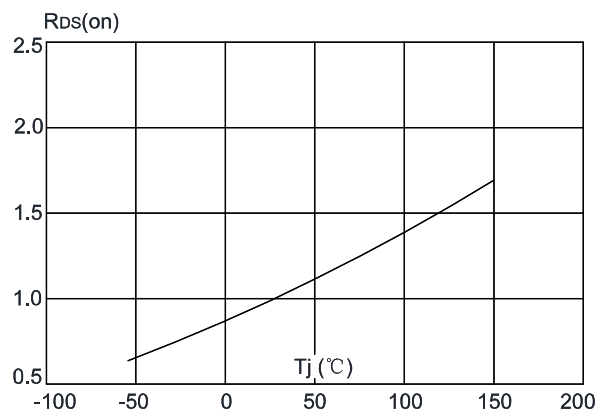


Figure 9: Maximum Safe Operating Area

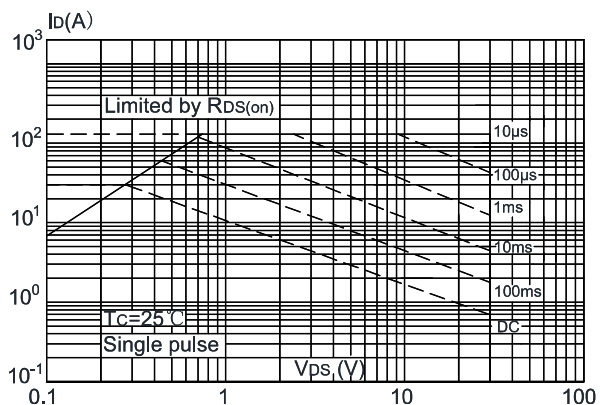


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

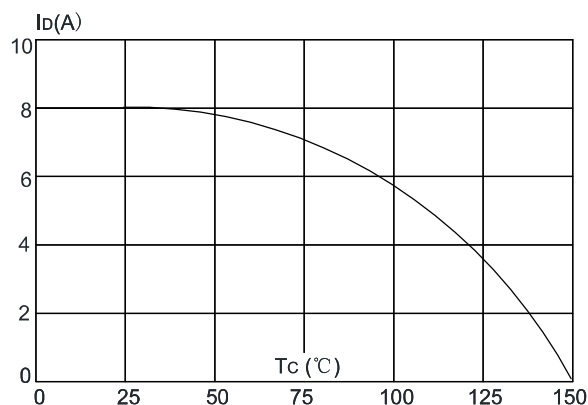
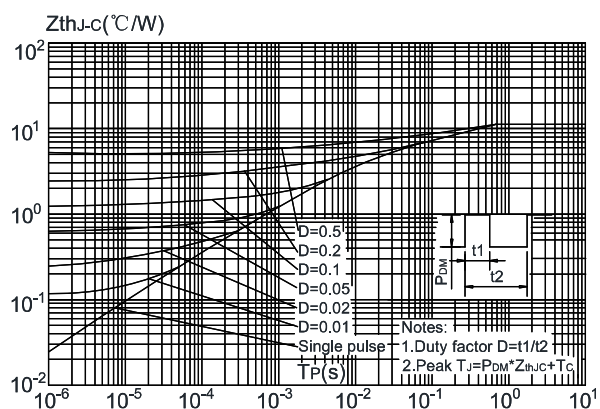


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



SOT-23-3 Package Information

